

METHOD FOR PREPARATION OF SEMICONDUCTIVE FILMS

Inventors: Quanxi Jia
832 Kristi
Los Alamos, New Mexico 87544

CITIZEN OF THE UNITED STATES OF AMERICA

Lin Song Li
1764 N Leverett Ave, Apt. 215
Fayetteville, AR 72703

CITIZEN OF CHINA

EXPRESS MAIL LABEL NO.: ET461826042US

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STATEMENT REGARDING FEDERAL RIGHTS

This invention was made with government support under Contract No. W-7405-
5 ENG-36 awarded by the U.S. Department of Energy. The government has certain rights
in the invention.

FIELD OF THE INVENTION

The present invention relates to a deposition technique for semiconductive films and
more particularly to the polymer assisted deposition of semiconductive films, especially
10 thin semiconductive films. The polymer assisted deposition can be accomplished in an
aqueous solution process.

BACKGROUND OF THE INVENTION

Semiconductive films are used for photovoltaic and electro-optical devices. Such
semiconductive materials have been previously deposited in the form of films by
15 techniques such as reactive sputtering, co-evaporation techniques and chemical vapor
deposition techniques.

Several methods of manufacturing thin-film solar cells are described by U.S.
Patent Nos. 4,735,644, 5,538,903 (a paste deposition process), 5,728,231, 5,828,117 and
5,994,163. Despite these various methods, improvements and new techniques have
20 continually been sought.

An object of the present invention is to provide a process of forming semiconductive
thin films through an initial chemical solution deposition method of metal oxide thin
films followed by conversion of the metal oxide to a sulfide, selenide, and the like.

SUMMARY OF THE INVENTION

To achieve the foregoing and other objects, and in accordance with the purposes of
the present invention, as embodied and broadly described herein, the present invention
provides for a process of preparing a semiconductive film including applying a solution
including a soluble polymer and a soluble metal precursor onto a substrate to form a
polymer and metal-containing layer thereon, treating said substrate including said
30 polymer and metal-containing layer for a time to form a coherent composite film, heating